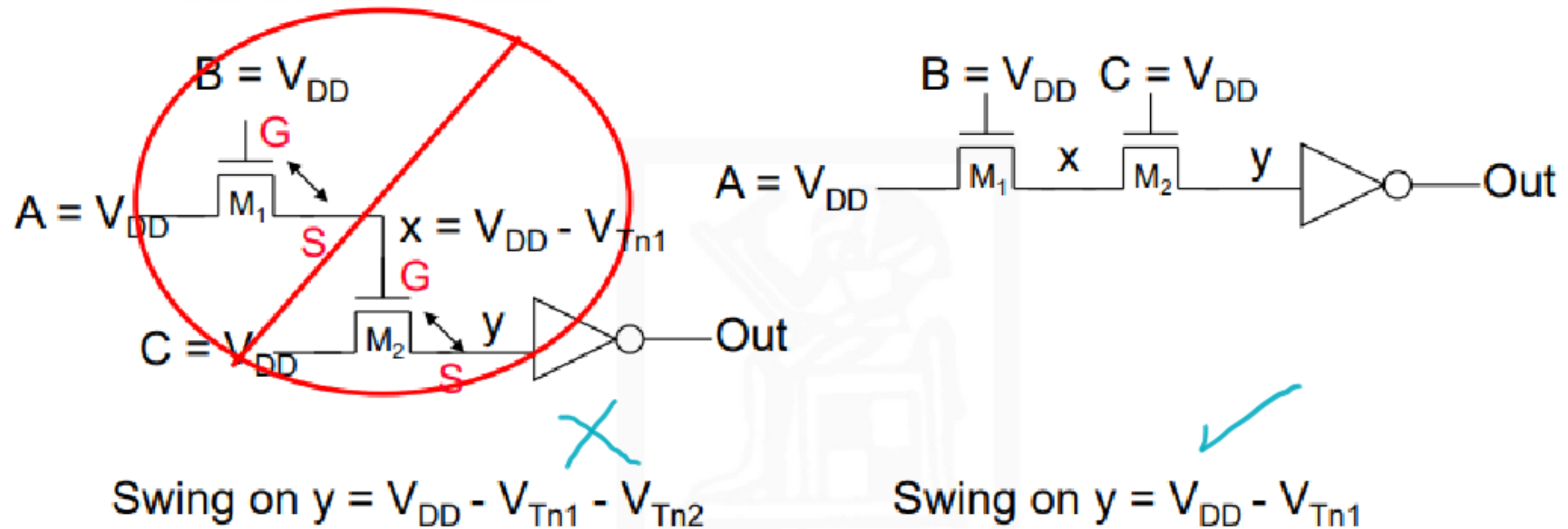


Cascaded NMOS Only PTs

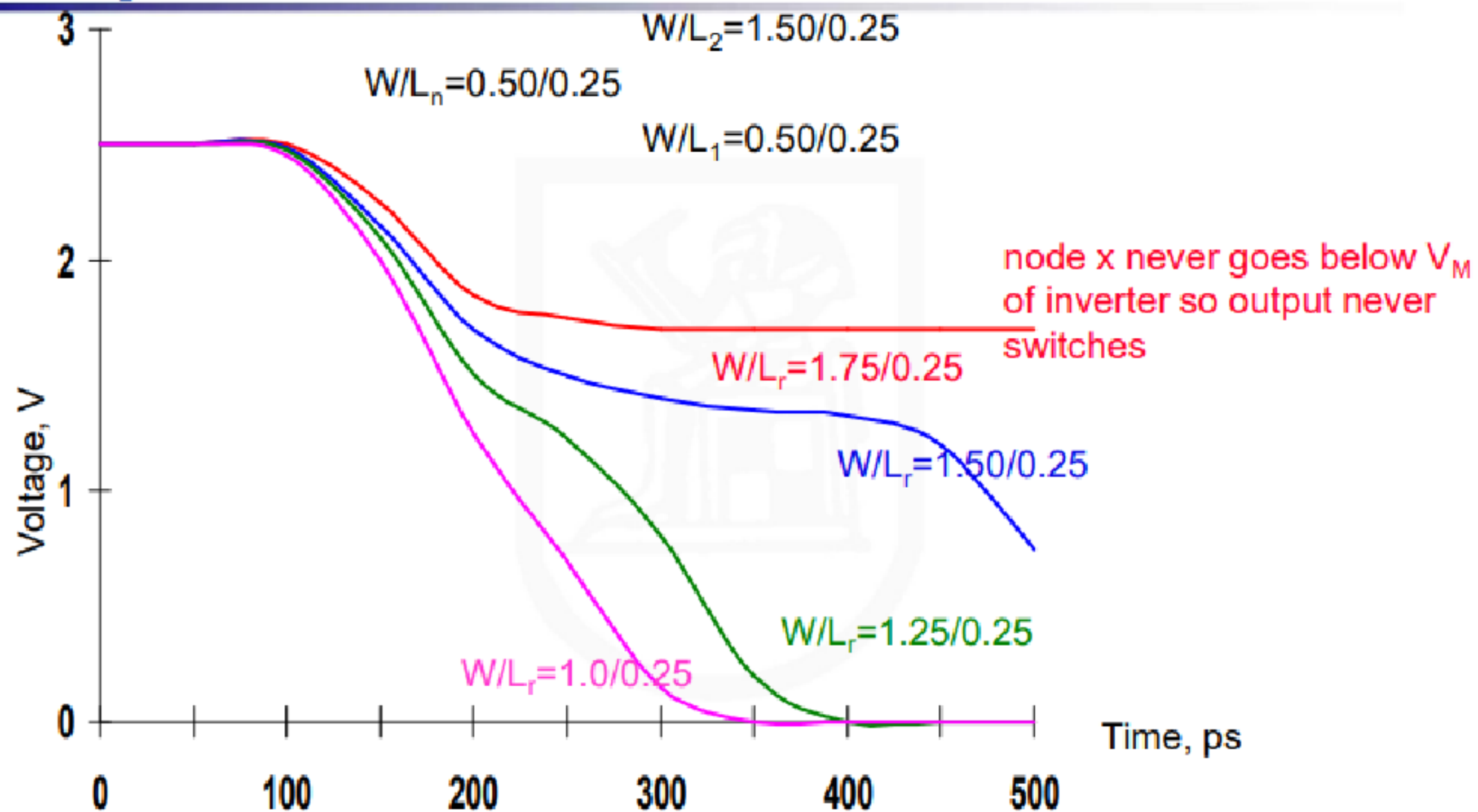


- ❑ Pass transistor gates should **never** be cascaded as on the left
- ❑ Logic on the right suffers from static power dissipation and reduced noise margins



- ❑ Full swing on x (due to Level Restorer) so no static power consumption by inverter
- ❑ No static backward current path through Level Restorer and PT since Restorer is only active when A is high
- **For correct operation M_r must be sized correctly (ratioed)**

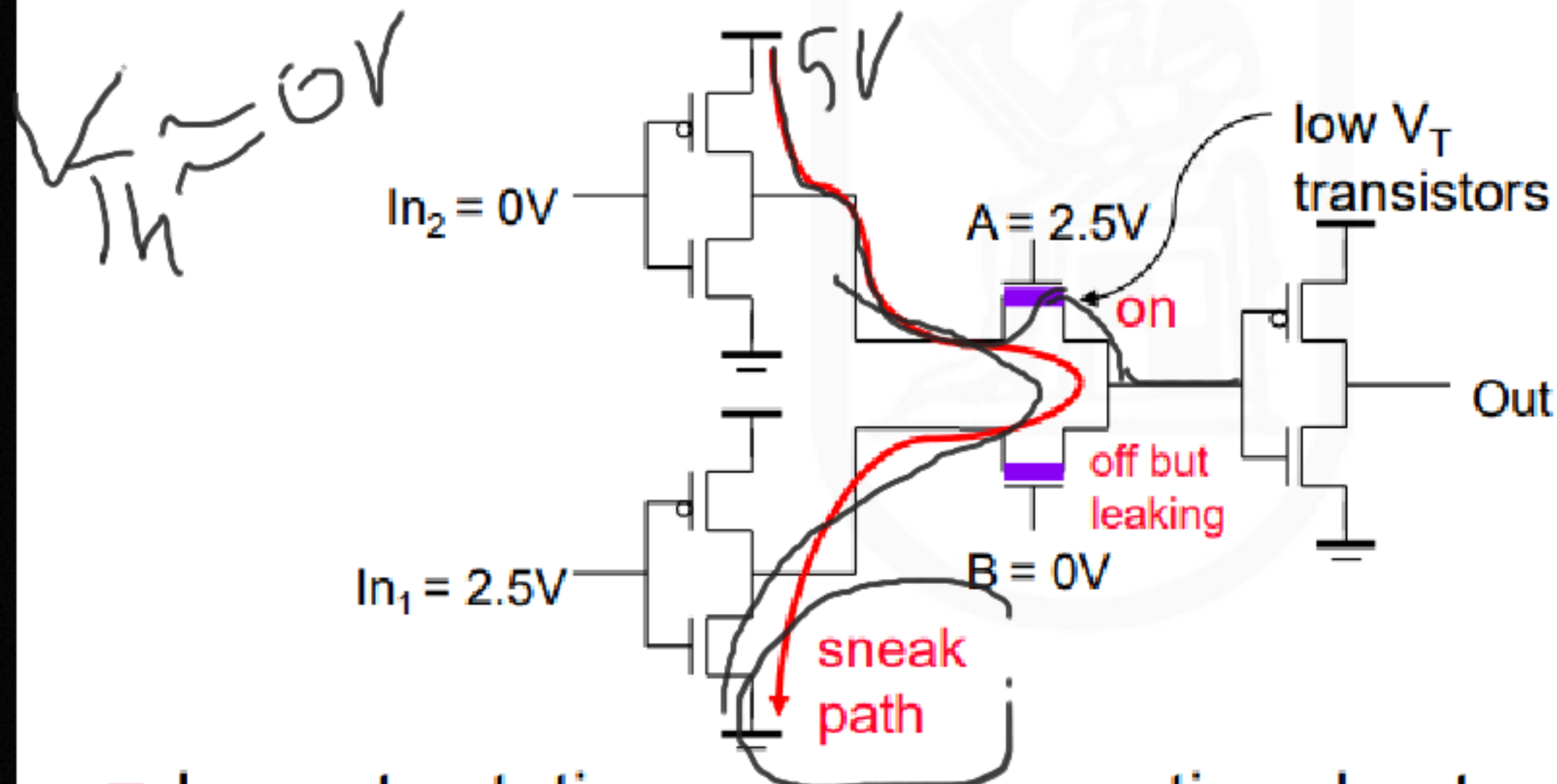
Transient Level Restorer Circuit Response



- ❑ Restorer has speed and power impacts: increases the cap at x, slowing down the gate; increases t_r (but decreases t_f)

Solution 2: Multiple V_T Transistors

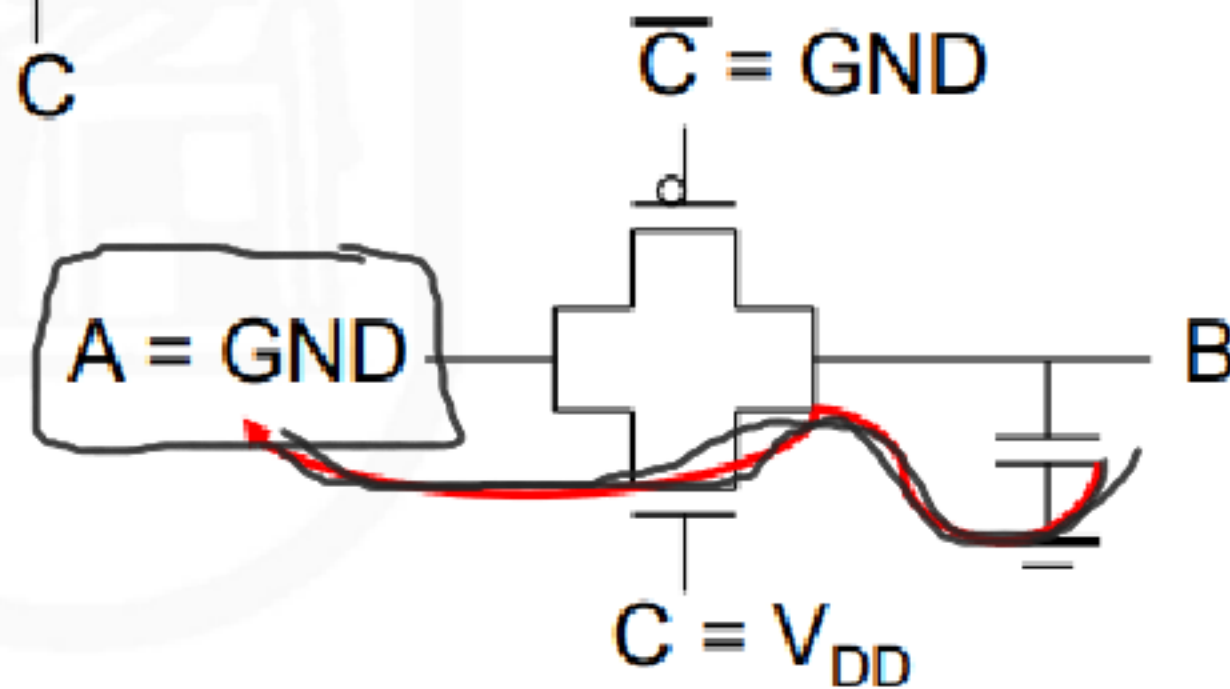
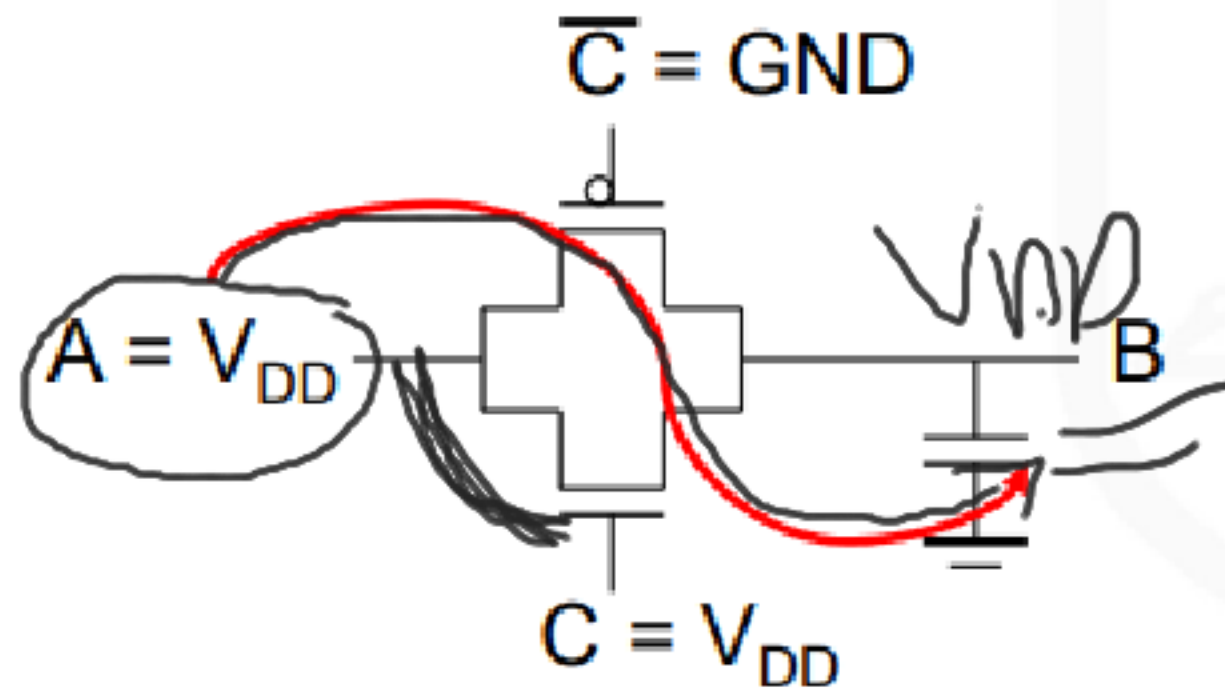
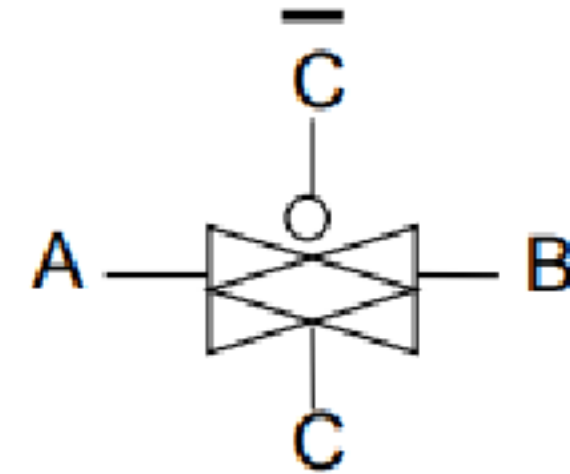
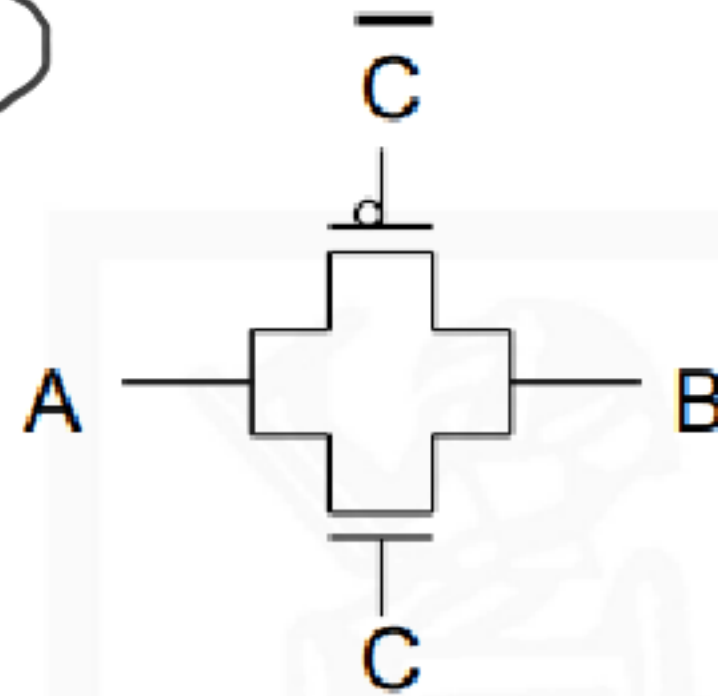
- Technology solution: Use (near) zero V_T devices for the NMOS PTs to eliminate *most* of the threshold drop (body effect still in force preventing full swing to V_{DD})



- Impacts static power consumption due to subthreshold currents flowing through the PTs (even if V_{GS} is below V_T)

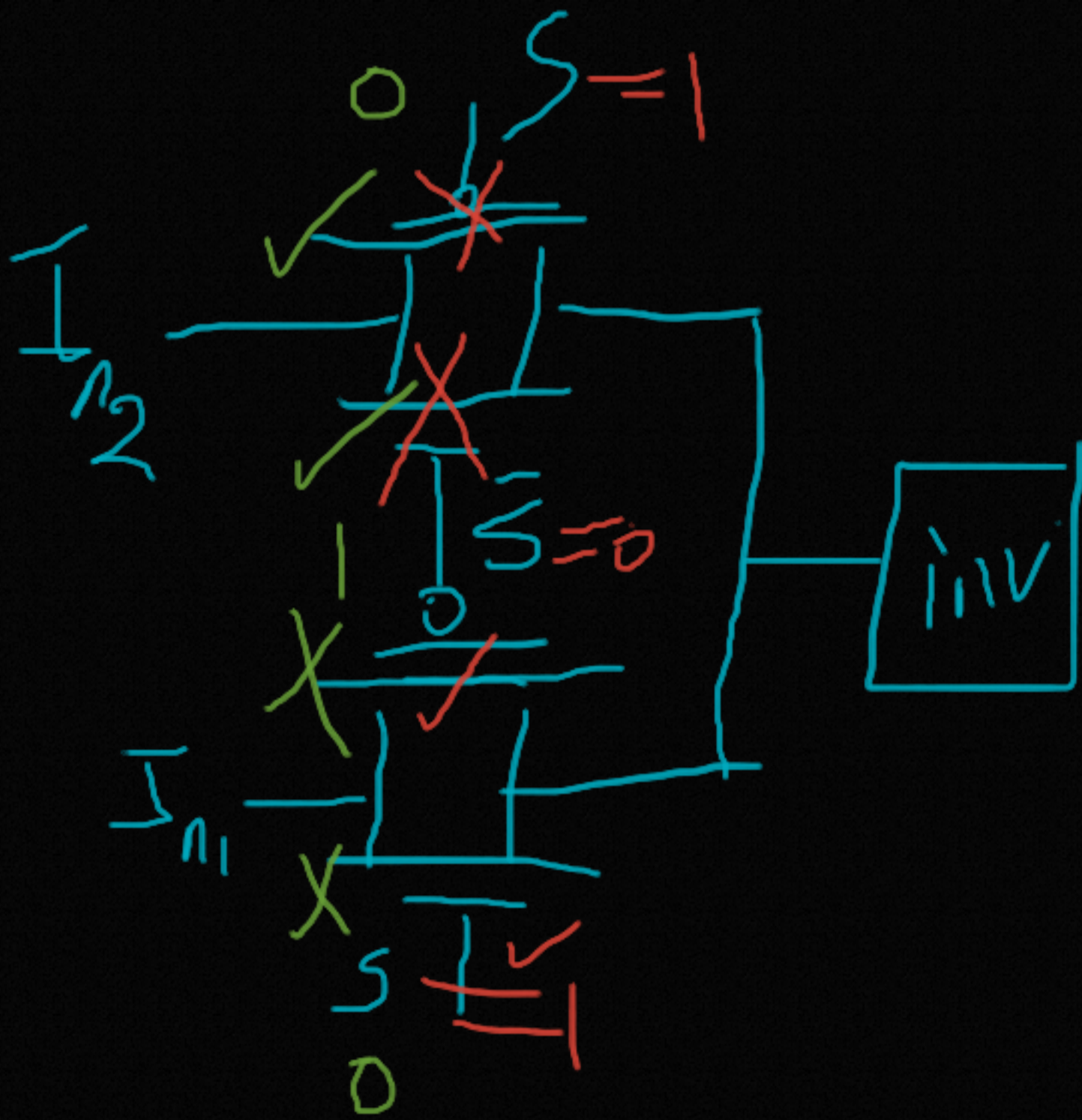
Solution 3: Transmission Gates (TGs)

- Most widely used solution

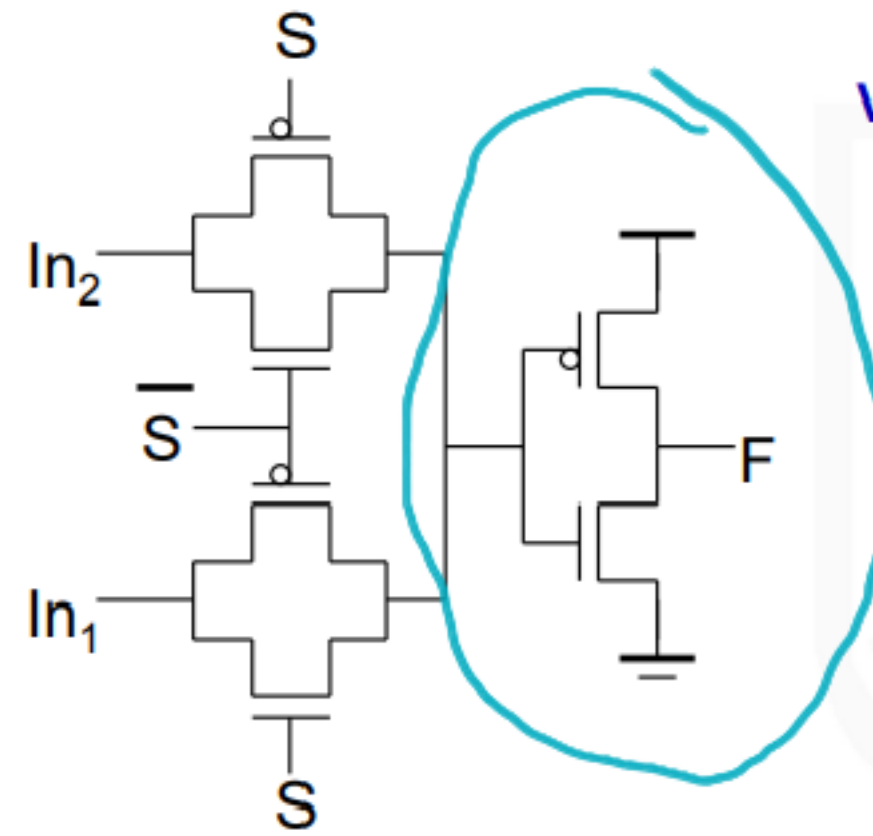


- Full swing bidirectional switch** controlled by the gate signal C , $A = B$ if $C = 1$

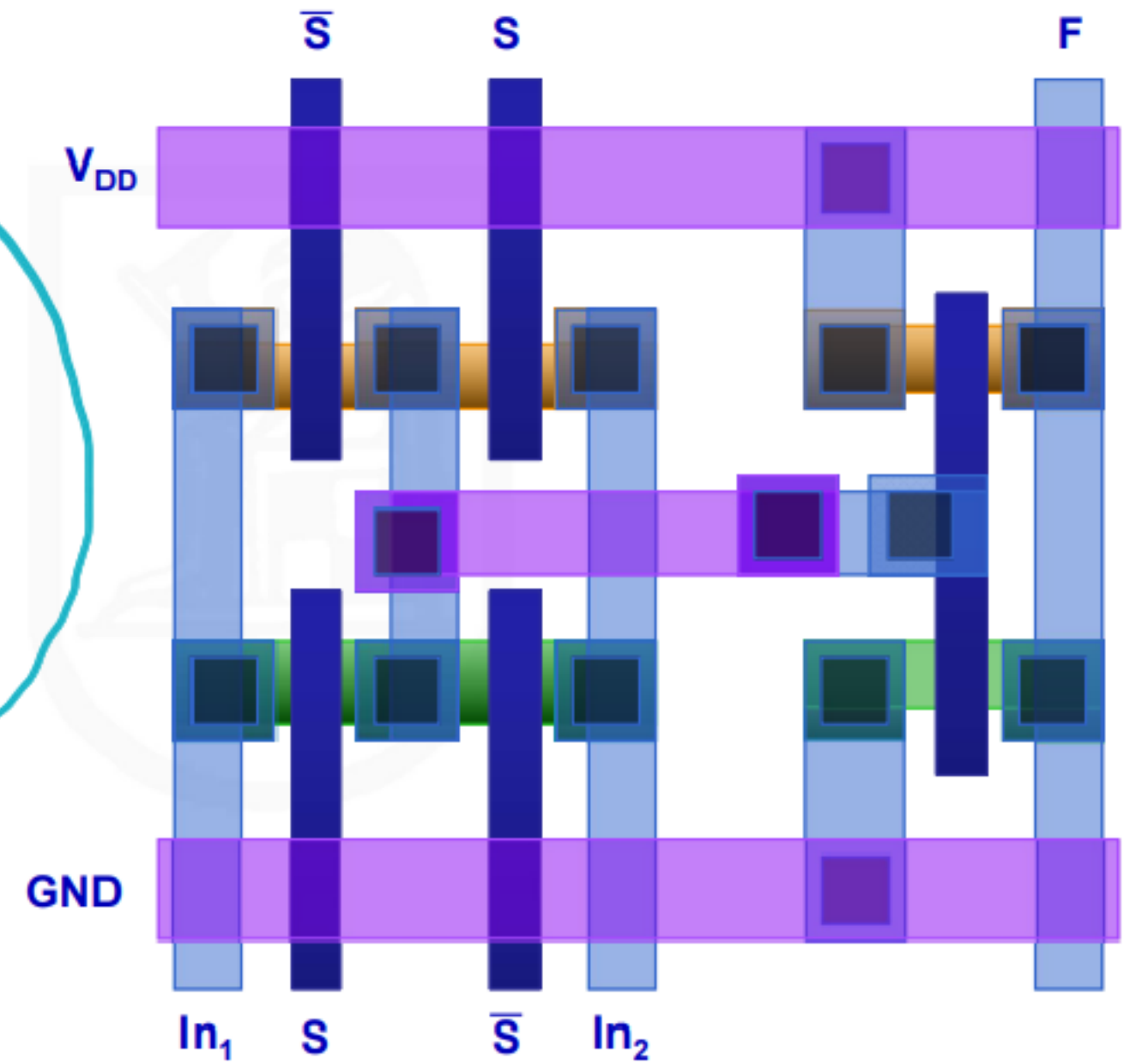
Handwritten notes in blue ink on the left margin: a large 'X' and the text '10p' and '5p'.



TG Multiplexer



$$F = \overline{(In_1 \bullet S + In_2 \bullet \overline{S})}$$



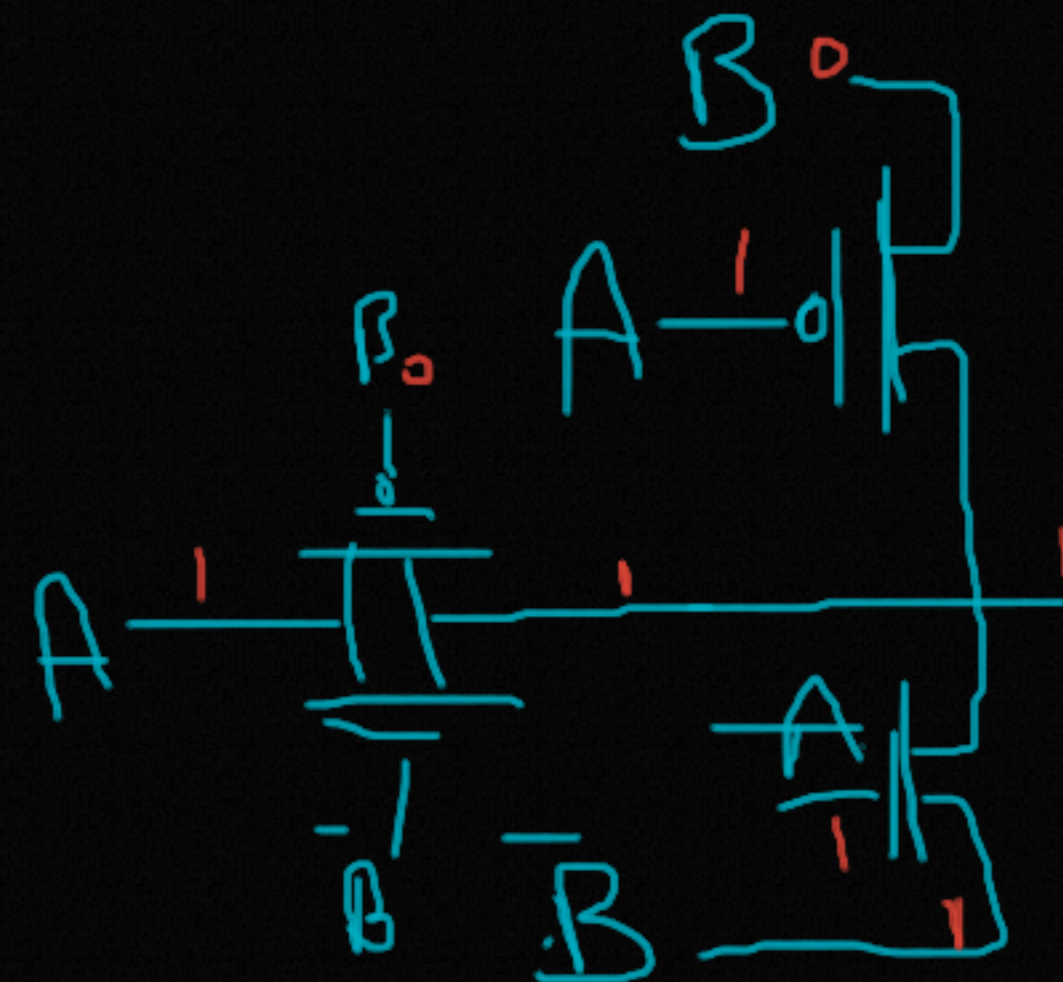
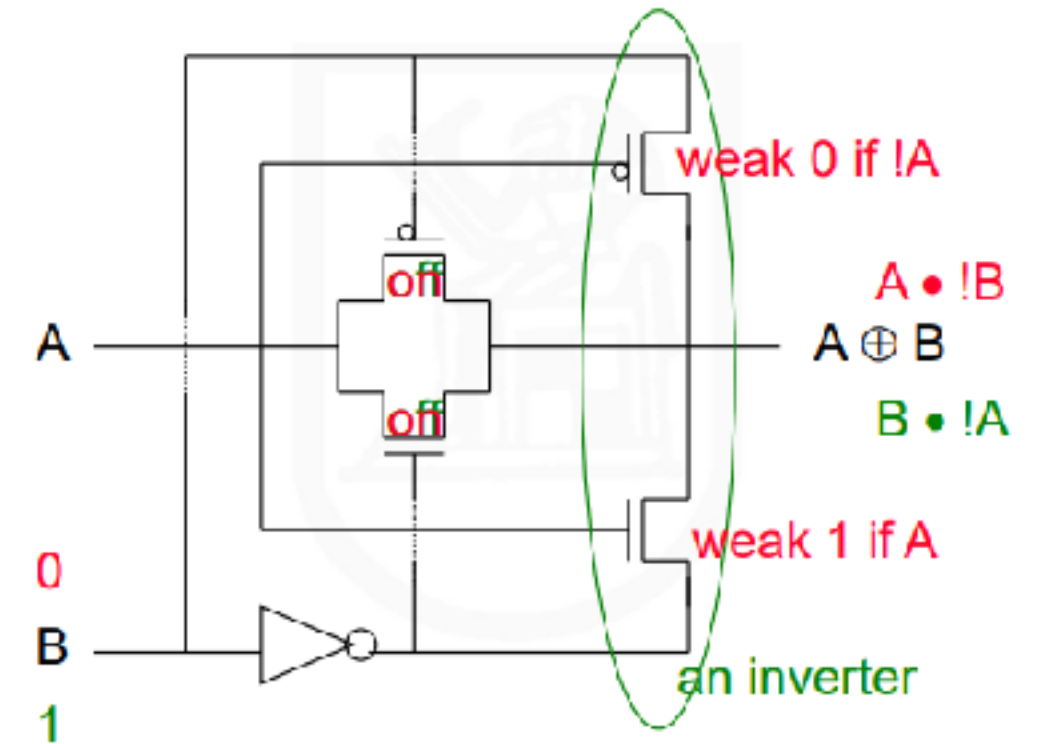
$$In_2 \overline{S} + In_1 S$$





A	B	G	V
0	0	0	✓
0	1	1	✓
1	0	1	✓
1	1	0	✓

Transmission Gate XOR



TG Full Adder

